



## 150-mW STEREO AUDIO POWER AMPLIFIER

### **FEATURES**

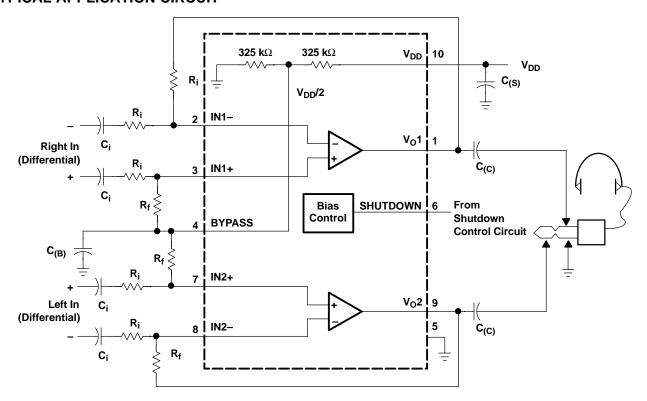
- 150 mW Stereo Output
- **Differential Inputs**
- **PC Power Supply Compatible** 
  - Fully Specified for 3.3 V and 5 V Operation
  - Operation to 2.5 V
- **Pop Reduction Circuitry**
- **Internal Mid-Rail Generation**
- Thermal and Short-Circuit Protection
- **Surface-Mount Packaging** 
  - PowerPAD™ MSOP

#### **DGQ PACKAGE** (TOP VIEW) 10 $\coprod V_{\mathsf{DD}}$ IN1-2 9 $\square$ V<sub>O</sub>2 IN1+[ 8 BYPASS [ 7 ∏IN2+ GND **TSHUTDOWN**

### **DESCRIPTION**

The TPA6112A2 is a stereo audio power amplifier with differential inputs packaged in a 10-pin PowerPAD MSOP package capable of delivering 150 mW of continuous RMS power per channel into 16-Ω loads. Amplifier gain is externally configured by means of two resistors per input channel and does not require external compensation for settings of 1 to 10.

### TYPICAL APPLICATION CIRCUIT



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **DESCRIPTION (CONTINUED)**

THD+N when driving an 16- $\Omega$  load from 5 V is 0.03% at 1 kHz, and less than 1% across the audio band of 20 Hz to 20 kHz. For 32- $\Omega$  loads, the THD+N is reduced to less than 0.02% at 1 kHz, and is less than 1% across the audio band of 20 Hz to 20 kHz. For 10-k $\Omega$  loads, the THD+N performance is 0.005% at 1 kHz, and less than 0.5% across the audio band of 20 Hz to 20 kHz.

### **AVAILABLE OPTIONS**

T <sub>A</sub>	PACKAGED DEVICE  MSOP <sup>(1)</sup>	MSOP SYMBOLIZATION
-40°C to 85°C	TPA6112A2DGQ	TI APD

(1) The DGQ package isavailable in left-ended tape and reel only (e.g., TPA6112A2DGQR).

#### **Terminal Functions**

TERMINAL		I/O	DESCRIPTION
NAME	NO	1/0	DESCRIPTION
BYPASS	4	I	Tap to voltage divider for internal mid-supply bias supply. Connect to a 0.1 $\mu$ F to 1 $\mu$ F low ESR capacitor for best performance.
GND	5	ı	GND is the ground connection.
IN1-	2	ı	IN1- is the negative input for channel 1.
IN1+	3	ı	IN1+ is the positive input for channel 1.
IN2-	8	ı	IN2- is the negative input for channel 2.
IN2+	7	ı	IN2+ is the positive input for channel 2.
SHUTDOWN	6	I	Puts the device in a low quiescent current mode when held high.
$V_{DD}$	10	I	V <sub>DD</sub> is the supply voltage terminal.
V <sub>O</sub> 1	1	0	V <sub>O</sub> 1 is the audio output for channel 1.
V <sub>O</sub> 2	9	0	V <sub>O</sub> 2 is the audio output for channel 2.

### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature (unless otherwise noted(1))

		UNITS
$V_{DD}$	Supply voltage	6 V
$V_{I}$	Input voltage	-0.3 V to V <sub>DD</sub> + 0.3 V
	Continuous total power dissipation	internally limited
$T_J$	Operating junction temperature range	-40°C to 150°C
T <sub>stg</sub>	Storage temperature range	-65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

<sup>(1)</sup> Stresses beyond thoselisted under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at theseor any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions forextended periods may affect device reliability.



### **DISSIPATION RATING TABLE**

PACKAGE	T <sub>A</sub> ≤ 25°C	DERATING FACTOR	T <sub>A</sub> = 70°C	T <sub>A</sub> = 85°C
	POWER RATING	ABOVE T <sub>A</sub> = 25°C	POWER RATING	POWER RATING
DGQ	2.14 W <sup>(1)</sup>	17.1 mW/°C	1.37 W	1.11 W

(1) Please see the Texas Instrumentsdocument, PowerPAD Thermally EnhancedPackage Application Report (literature number SLMA002), for moreinformation on the PowerPAD package. The thermal data was measured on a PCBlayout based on the information in the section entitled Texas Instruments Recommended Board for PowerPAD on page 33 of the before mentioneddocument.

### **RECOMMENDED OPERATING CONDITIONS**

		MIN	MAX	UNIT
$V_{DD}$	Supply voltage	2.5	5.5	V
T <sub>A</sub>	Operating free-air temperature	-40	85	°C
V <sub>IH</sub> , (SHUTDOWN)	High-level input voltage	60% x V <sub>DD</sub>		V
V <sub>IL</sub> , (SHUTDOWN)	Low-level input voltage		25% x V <sub>DD</sub>	V

### DC ELECTRICAL CHARACTERISTICS

At  $T_A = 25^{\circ}C$ ,  $V_{DD} = 2.5 \text{ V}$  (Unless Otherwise Noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>oo</sub>	Output offset voltage	A <sub>V</sub> = 2 V/V			15	mV
PSRR	Power supply rejection ratio	V <sub>DD</sub> = 3.2 V to 3.4 V		83		dB
I <sub>DD</sub>	Supply current	SHUTDOWN = 0 V		1.5	3	mA
I <sub>DD(SD)</sub>	Supply current in SHUTDOWN mode	SHUTDOWN = V <sub>DD</sub>		10	50	μΑ
Z <sub>i</sub>	Input impedance			>1		$M\Omega$

### **AC OPERATING CHARACTERISTICS**

 $V_{DD}$  = 3.3 V,  $T_A$  = 25°C,  $R_L$  = 16  $\Omega$ 

	PARAMETER	TEST CONDITIONS	MIN TYP M	AX UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	60	mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 40 mW, 20 - 20 kHz	0.4%	
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 5%	> 20	kHz
	Phase margin	Open loop	96°	
	Supply ripple rejection ratio	f = 1 kHz	71	dB
	Channel/channel output separation	f = 1 kHz	89	dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 50 mW, A <sub>V</sub> = 1	100	dB
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1	11	μV(rms)

### DC ELECTRICAL CHARACTERISTICS

At  $T_A = 25^{\circ}C$ ,  $V_{DD} = 5$  .5 V (Unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>OO</sub>	Output offset voltage	A <sub>V</sub> = 2 V/V			15	mV
PSRR	Power supply rejection ratio	V <sub>DD</sub> = 4.9 V to 5.1 V		76		dB
I <sub>DD</sub>	Supply current	SHUTDOWN = 0 V		1.5	3	mA
I <sub>DD(SD)</sub>	Supply current in SHUTDOWN mode	SHUTDOWN = V <sub>DD</sub>		60	100	μΑ
I <sub>IH</sub>	High-level input current (SHUTDOWN)	$V_{DD} = 5.5 \text{ V}, V_{I} = V_{DD}$			1	μA
I <sub>IL</sub>	Low-level input current (SHUTDOWN)	$V_{DD} = 5.5 \text{ V}, V_{I} = 0 \text{ V}$			1	μA
Z <sub>i</sub>	Input impedance			>1		$M\Omega$



### **AC OPERATING CHARACTERISTICS**

 $V_{DD}$  = 5 V,  $T_A$  = 25°C,  $R_L$  = 16  $\Omega$ 

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	150		mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 100 mW, 20 - 20 kHz	0.6%		
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 5%	> 20		kHz
	Phase margin	Open loop	96°		
	Supply ripple rejection ratio	f = 1 kHz	61		dB
	Channel/channel output separation	f = 1 kHz	90		dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 100 mW, A <sub>V</sub> = 1	100		dB
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1	11.7		μV(rms)

### **AC OPERATING CHARACTERISTICS**

 $V_{DD}$  = 3.3 V,  $T_A$  = 25°C,  $R_L$  = 32  $\Omega$ 

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	40		mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 30 mW, 20 - 20 kHz	0.4%		
B <sub>OM</sub>	Maximum output power BW	A <sub>V</sub> = 10, THD < 2%	> 20		kHz
	Phase margin	Open loop	96°		
	Supply ripple rejection ratio	f = 1 kHz	71		dB
	Channel/channel output separation	f = 1 kHz	95		dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 40 mW, A <sub>V</sub> = 1	100		dB
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1	11		μV(rms)

### **AC OPERATING CHARACTERISTICS**

 $V_{DD}$  = 5 V,  $T_A$  = 25°C,  $R_L$  = 32  $\Omega$ 

	PARAMETER	TEST CONDITIONS	MIN TYP N	IAX UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	90	mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 60 mW, 20 - 20 kHz	0.4%	
B <sub>OM</sub>	Maximum output power BW	A <sub>V</sub> = 10, THD < 2%	> 20	kHz
	Phase margin	Open loop	97°	
	Supply ripple rejection ratio	f = 1 kHz	61	dB
	Channel/channel output separation	f = 1 kHz	98	dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 90 mW, A <sub>V</sub> = 1	100	dB
V <sub>n</sub>	Noise output voltage	A <sub>V</sub> = 1	11.7	μV(rms)

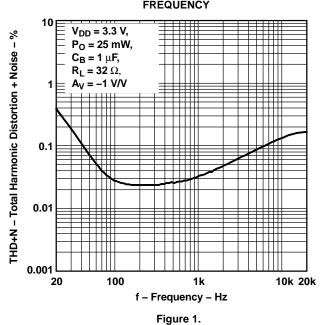


### **TYPICAL CHARACTERISTICS**

### **Table of Graphs**

			FIGURE
TUD.N	Total harmonic distantian also unica	vs Frequency	1, 3, 5, 6, 7, 9, 11, 13,
THD+N	Total harmonic distortion plus noise	vs Output power	2, 4, 8, 10, 12, 14
	Supply ripple rejection ratio	vs Frequency	15, 16
V <sub>n</sub>	Output noise voltage	vs Frequency	17, 18
	Crosstalk	vs Frequency	19 - 24
	Shutdown attenuation	vs Frequency	25, 26
	Open-loop gain and phase margin	vs Frequency	27, 28
	Output power	vs Load resistance	29, 30,
I <sub>DD</sub>	Supply current	vs Supply voltage	31
SNR	Signal-to-noise ratio	vs Voltage gain	32
	Power dissipation/amplifier	vs Load power	33, 34

# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



## TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

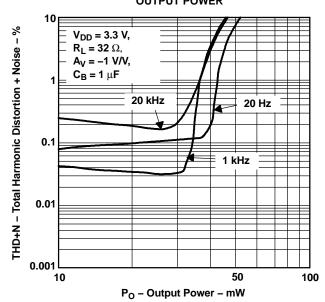
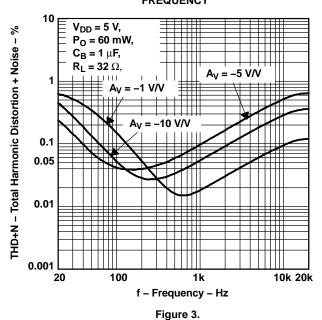


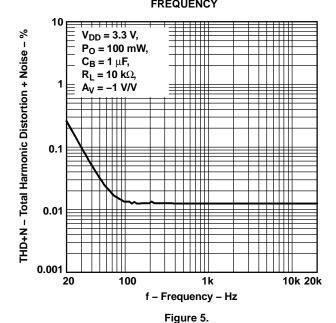
Figure 2.



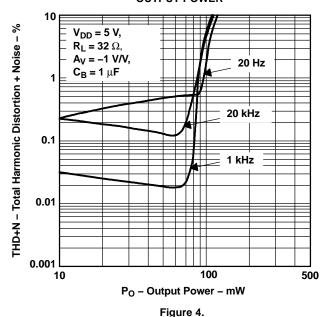
## TOTAL HARMONIC DISTORTION + NOISE VS FREQUENCY



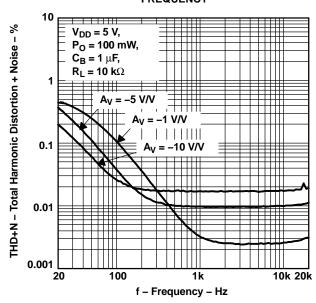
# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



## TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

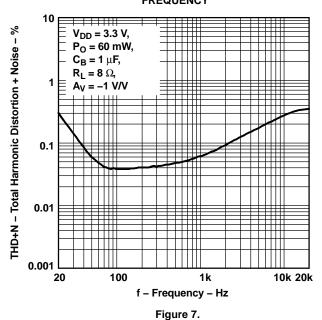


# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

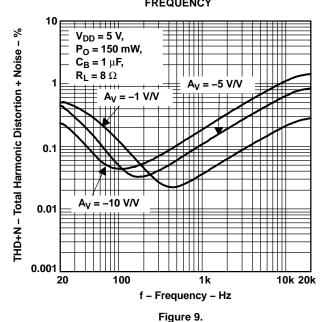




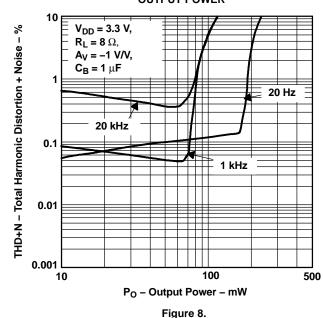
## TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



## TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER



### TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

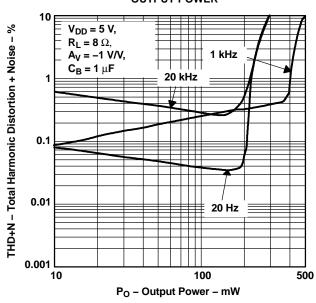
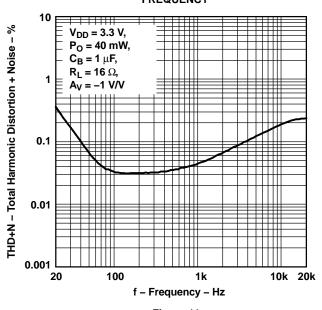


Figure 10.



## TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



### Figure 11.

## TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

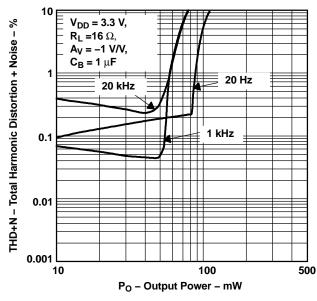


Figure 12.

# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

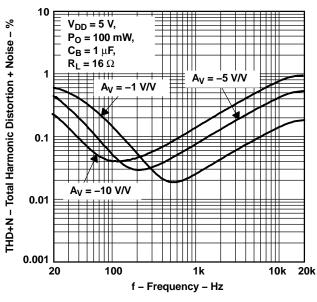


Figure 13.

### TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

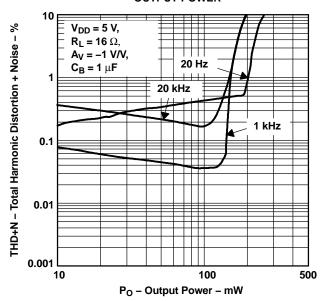
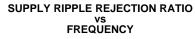


Figure 14.





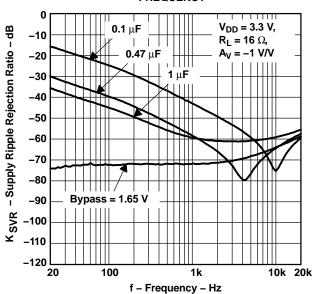


Figure 15.

## SUPPLY RIPPLE REJECTION RATIO vs FREQUENCY

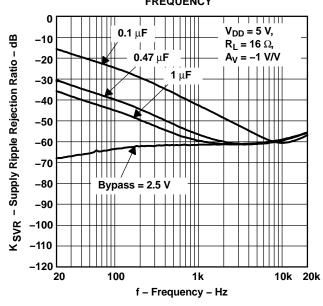


Figure 16.

## OUTPUT NOISE VOLTAGE VS FREQUENCY

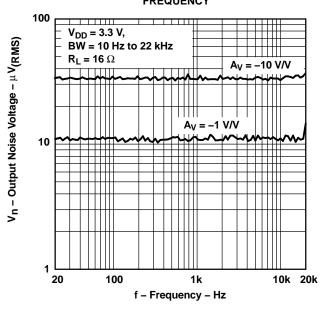


Figure 17.

# OUTPUT NOISE VOLTAGE vs FREQUENCY

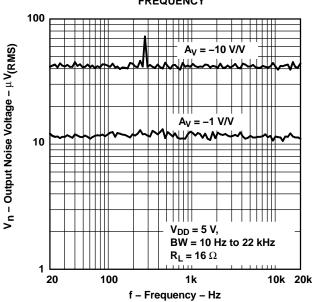
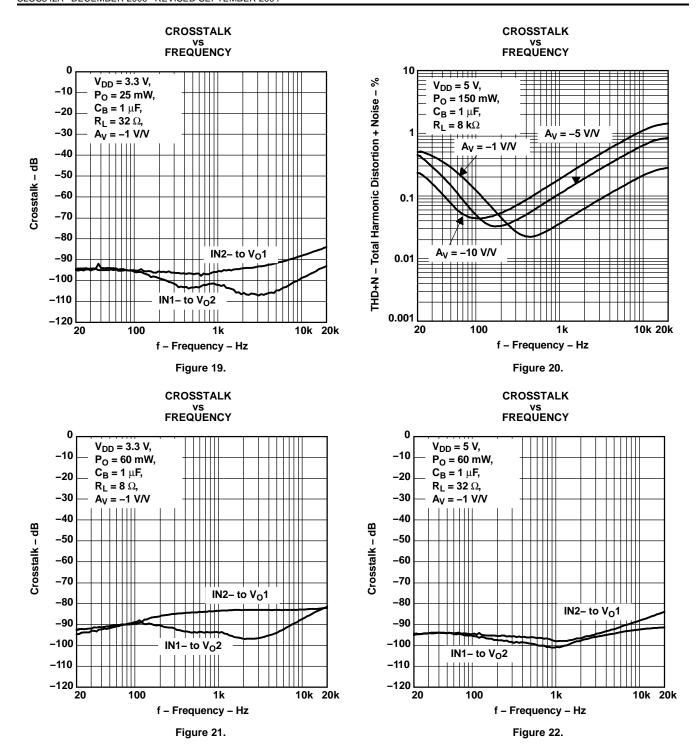


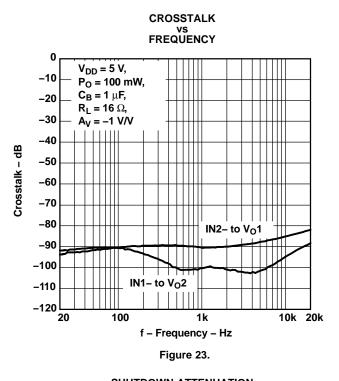
Figure 18.

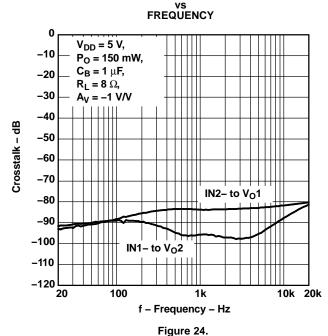




**CROSSTALK** 

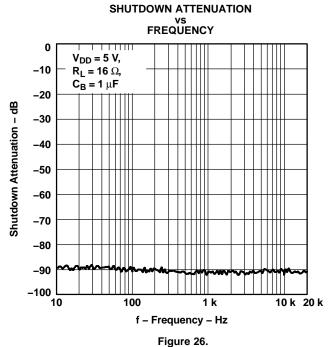






### **SHUTDOWN ATTENUATION** vs FREQUENCY 0 $V_{DD} = 3.3 V$ , $R_L = 16 \Omega$ , -10 $C_B = 1 \mu F$ -20 Shutdown Attenuation – dB -30 -40 -50 -60 -70 -80 -90 -100 100 1 k 10 k 20 k 10 f - Frequency - Hz

Figure 25.



-40

1 k

10 k



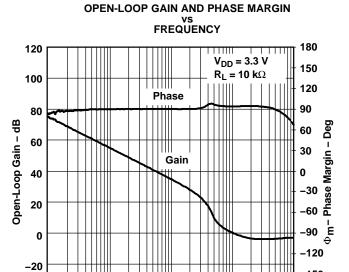


Figure 27.

1 M

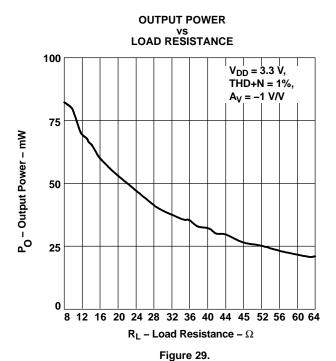
100 k

f - Frequency - Hz

-150

-180

10 M



OPEN-LOOP GAIN AND PHASE MARGIN
VS
FREQUENCY

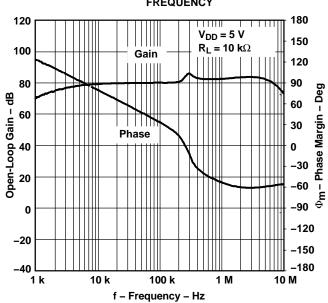
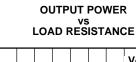


Figure 28.



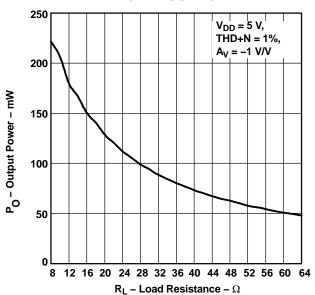
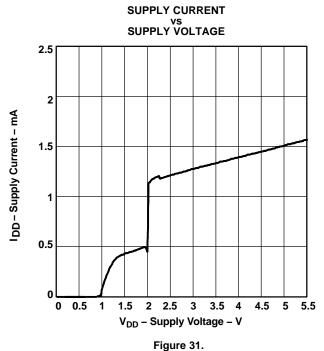
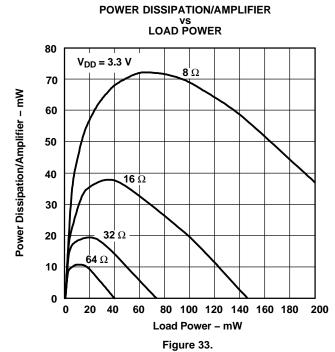


Figure 30.

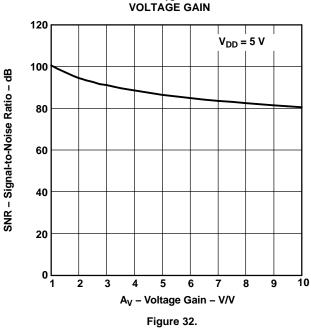




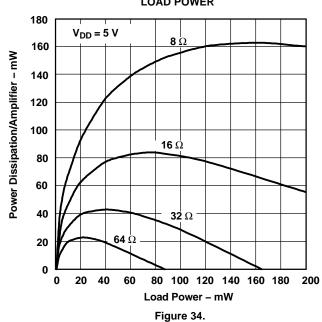




#### SIGNAL-TO-NOISE RATIO VS VOLTAGE GAIN



## POWER DISSIPATION/AMPLIFIER vs LOAD POWER





### APPLICATION INFORMATION

### GAIN SETTING RESISTORS, R, and R;

The gain for the TPA6112A2 is set by resistors  $R_f$  and  $R_i$  according to Equation 1.

$$Gain = -\left(\frac{R_f}{R_i}\right)$$
 (1)

Given that the TPA6112A2 is a MOS amplifier, the input impedance is very high. Consequently input leakage currents are not generally a concern. However, noise in the circuit increases as the value of  $R_{\rm f}$  increases. In addition, a certain range of  $R_{\rm f}$  values is required for proper start-up operation of the amplifier. Considering these factors, it is recommended that the effective impedance seen by the inverting node of the amplifier be set between 5 k $\Omega$  and 20 k $\Omega$ . The effective impedance is calculated using Equation 2.

Effective Impedance = 
$$\frac{R_f R_i}{R_f + R_i}$$
 (2)

For example, if the input resistance is 20  $k\Omega$  and the feedback resistor is 20  $k\Omega$ , the gain of the amplifier is -1, and the effective impedance at the inverting terminal is 10  $k\Omega$ , a value within the recommended range.

For high performance applications, metal-film resistors are recommended because they tend to have lower noise levels than carbon resistors. For values of  $R_{\rm f}$  above 50  $k\Omega,$  the amplifier tends to become unstable due to a pole formed from  $R_{\rm f}$  and the inherent input capacitance of the MOS input structure. For this reason, a small compensation capacitor of approximately 5 pF should be placed in parallel with  $R_{\rm f}.$  This, in effect, creates a low-pass filter network with the cutoff frequency defined by Equation 3.

$$f_{c(lowpass)} = \frac{1}{2\pi R_f C_F}$$
 (3)

For example, if  $R_{\rm f}$  is 100  $k\Omega$  and  $C_{\rm F}$  is 5 pF then  $f_{c(lowpass)}$  is 318 kHz, which is well outside the audio range.

### INPUT CAPACITOR, C;

In the typical application, an input capacitor,  $C_i$ , is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case,  $C_i$  and  $R_i$  form a high-pass filter with the corner frequency determined in Equation 4.

$$f_{c(highpass)} = \frac{1}{2\pi R_i C_i}$$
 (4)

The value of  $C_i$  directly affects the bass (low frequency) performance of the circuit. Consider the example where  $R_i$  is 20 k $\Omega$  and the specification calls for a flat bass response down to 20 Hz. Equation 4 is reconfigured as Equation 5.

$$C_{i} = \frac{1}{2\pi R_{i} f_{c(highpass)}}$$
 (5)

In this example,  $C_i$  is 0.40  $\mu F$ , so one would likely choose a value in the range of 0.47  $\mu F$  to 1  $\mu F$ . A further consideration for this capacitor is the leakage path from the input source through the input network formed by  $R_i$ ,  $C_i$ , and the feedback resistor ( $R_f$ ) to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom, especially in high-gain applications (gain >10). For this reason a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, connect the positive side of the capacitor to the amplifier input in most applications. The dc level there is held at  $V_{DD}/2$ —likely higher than the source dc level. It is important to confirm the capacitor polarity in the application.

### POWER SUPPLY DECOUPLING, C(S)

The TPA6112A2 is a high-performance CMOS audio amplifier that requires adequate power-supply decoupling to minimize the output total harmonic distortion (THD). Power-supply decoupling also prevents oscillations when long lead lengths are used between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1 µF, placed as close as possible to the device V<sub>DD</sub> lead, works best. For filtering lower-frequency noise signals, a larger aluminum electrolytic capacitor of 10 µF or greater placed near the power amplifier is recommended.



### MIDRAIL BYPASS CAPACITOR, C(B)

The midrail bypass capacitor,  $C_{(B)}$ , serves several important functions. During start up,  $C_{(B)}$  determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so low it can not be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a 230-k $\Omega$  source inside the amplifier. To keep the start-up pop as low as possible, maintain the relationship shown in Equation 6.

$$\frac{1}{\left(C_{(B)} \times 230 \text{ k}\Omega\right)} \leq \frac{1}{\left(C_{i}R_{i}\right)}$$
(6)

Consider an example circuit where  $C_{(B)}$  is 1  $\mu F,~C_i$  is 1  $\mu F,~and~R_i$  is 20  $k\Omega.$  Substituting these values into the equation 9 results in:  $6.25 \le 50$  which satisfies the rule. Bypass capacitor,  $C_{(B)},~values~of~0.1~\mu F~to~1~\mu F$  ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.

### OUTPUT COUPLING CAPACITOR, C(C)

In a typical single-supply, single-ended (SE) configuration, an output coupling capacitor ( $C_{(C)}$ ) is required to block the dc bias at the output of the amplifier, thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load form a high-pass filter governed by Equation 7.

$$f_{C} = \frac{1}{2\pi R_{L} C_{(C)}} \tag{7}$$

The main disadvantage, from a performance stand-point, is that the typically-small load impedance drives the low-frequency corner higher. Large values of  $C_{(C)}$  are required to pass low frequencies into the load. Consider the example where a  $C_{(C)}$  of 68  $\mu F$  is chosen and loads vary from 32  $\Omega$  to 47  $k\Omega.$  Table 1 summarizes the frequency response characteristics of each configuration.

Table 1. Common Load Impedances vs Low-Frequency Output Characteristics in SE Mode

R <sub>L</sub>	C <sub>(C)</sub>	LOWEST FREQUENCY
32 Ω	68 µF	73 Hz
10,000 Ω	68 µF	0.23 Hz
47,000 Ω	68 µF	0.05 Hz

As Table 1 indicates, headphone response is adequate, and drive into line level inputs (a home stereo for example) is very good.

The output coupling capacitor required in single-supply SE mode also places additional constraints on the selection of other components in the amplifier circuit. With the rules described earlier still valid, add the following relationship:

$$\frac{1}{\left(C_{(B)} \times 230 \text{ k}\Omega\right)} \le \frac{1}{\left(C_{i}R_{i}\right)} \le \frac{1}{R_{L}C_{(C)}}$$
(8)

### **USING LOW-ESR CAPACITORS**

Low-ESR capacitors are recommended throughout this application. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor

### 5-V VERSUS 3.3-V OPERATION

The TPA6112A2 was designed for operation over a supply range of 2.5 V to 5.5 V. This data sheet provides full specifications for 5-V and 3.3-V operation, since these are considered to be the two most common supply voltages. There are no special considerations for 3.3-V versus 5-V operation as far as supply bypassing, gain setting, or stability. The most important consideration is that of output power. Each amplifier in theTPA6112A2 can produce a maximum voltage swing of V<sub>DD</sub>— 1 V. This means, for 3.3-V operation, clipping starts to occur when V<sub>O(PP)</sub> = 2.3 V as opposed when V<sub>O(PP)</sub> = 4 V while operating at 5 V. The reduced voltage swing subsequently reduces maximum output power into the load before distortion becomes significant.

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### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
TPA6112A2DGQ	Active	Production	HVSSOP (DGQ)   10	80   TUBE	Yes	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	APD
TPA6112A2DGQ.A	Active	Production	HVSSOP (DGQ)   10	80   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	APD
TPA6112A2DGQR	Active	Production	HVSSOP (DGQ)   10	2500   LARGE T&R	Yes	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	APD
TPA6112A2DGQR.A	Active	Production	HVSSOP (DGQ)   10	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	APD
TPA6112A2DGQRG4	Active	Production	HVSSOP (DGQ)   10	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	APD

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

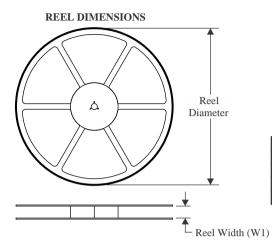
<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

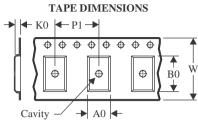
<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

## **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

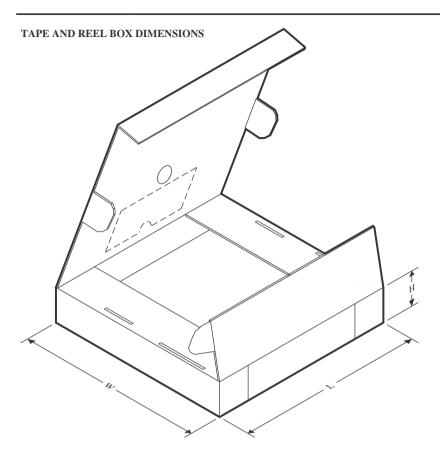
### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA6112A2DGQR	HVSSOP	DGQ	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TPA6112A2DGQR	HVSSOP	DGQ	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

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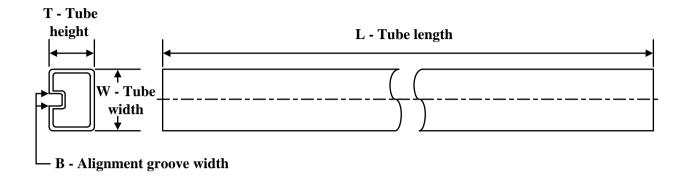
### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TPA6112A2DGQR	HVSSOP	DGQ	10	2500	364.0	364.0	27.0	
TPA6112A2DGQR	HVSSOP	DGQ	10	2500	358.0	335.0	35.0	

## **PACKAGE MATERIALS INFORMATION**

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### **TUBE**

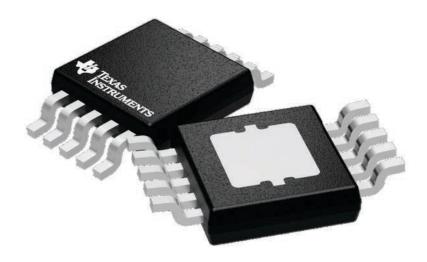


### \*All dimensions are nominal

ĺ	Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
ĺ	TPA6112A2DGQ	DGQ	HVSSOP	10	80	330	6.55	500	2.88
ĺ	TPA6112A2DGQ.A	DGQ	HVSSOP	10	80	330	6.55	500	2.88

3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE



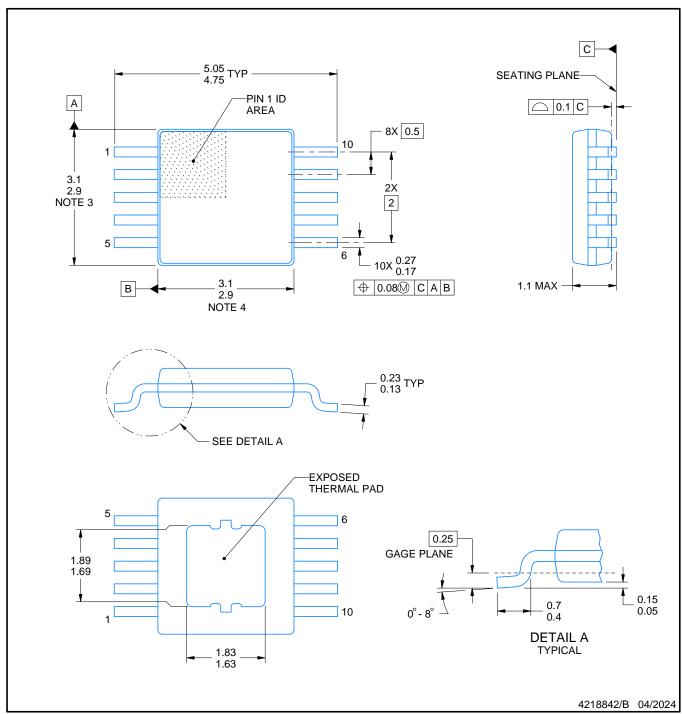
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224775/A





PLASTIC SMALL OUTLINE



### PowerPAD is a trademark of Texas Instruments.

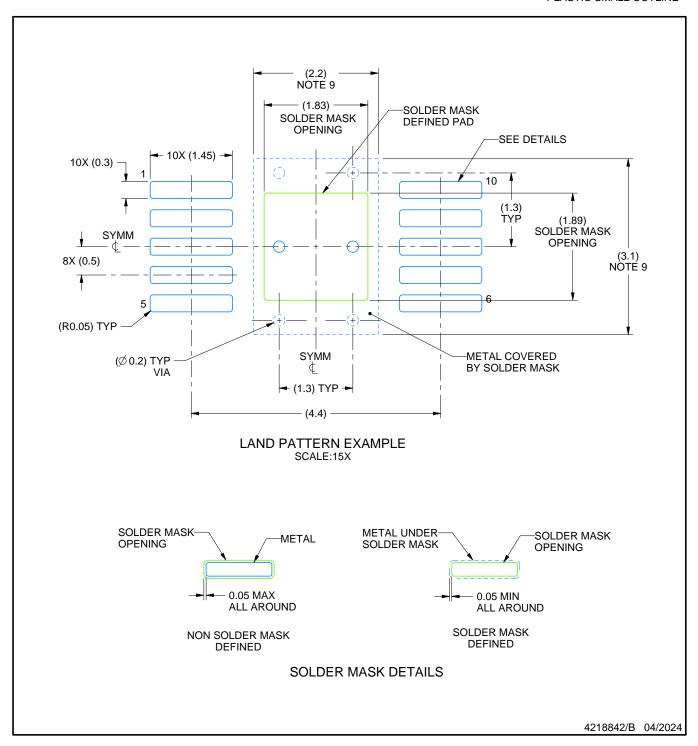
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187, variation BA-T.



PLASTIC SMALL OUTLINE

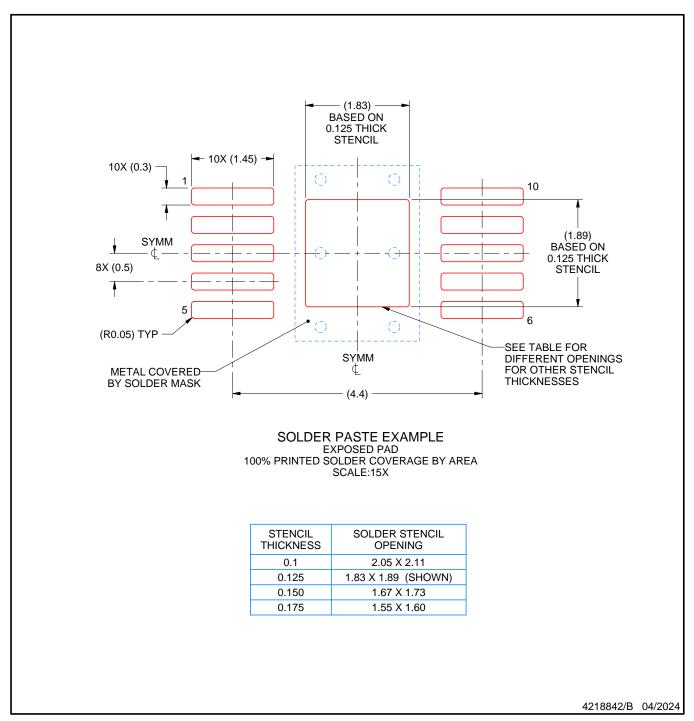


### NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
- 9. Size of metal pad may vary due to creepage requirement.



PLASTIC SMALL OUTLINE



### NOTES: (continued)

- 10. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 11. Board assembly site may have different recommendations for stencil design.



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